

2N3494
2N3495

SILICON
PNP TRANSISTORS



TO-39 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3494 and 2N3495 are silicon PNP transistors designed for general purpose amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Power Dissipation ($T_C=25^\circ\text{C}$)
Operating and Storage Junction Temperature

SYMBOL	2N3494	2N3495	UNITS
V_{CBO}	80	120	V
V_{CEO}	80	120	V
V_{EBO}		4.5	V
I_C		100	mA
P_D		0.6	W
P_D		3.0	W
T_J, T_{stg}		-65 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3494		2N3495		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=50\text{V}$ (2N3494)	-	100	-	-	nA
I_{CBO}	$V_{CB}=90\text{V}$ (2N3495)	-	-	-	100	nA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	25	-	25	nA
BV_{CBO}	$I_C=10\mu\text{A}$	80	-	120	-	V
BV_{CEO}	$I_C=10\text{mA}$	80	-	120	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	4.5	-	4.5	-	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	0.3	-	0.35	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.6	0.9	0.6	0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$	35	-	35	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	40	-	40	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	40	-	40	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	40	-	40	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=100\text{mA}$	35	-	-	-	
f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	200	-	150	-	MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$	-	7.0	-	6.0	pF
C_{ib}	$V_{EB}=2.0\text{V}, I_C=0, f=100\text{kHz}$	-	30	-	30	pF
h_{ie}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	0.1	1.2	0.1	1.2	k Ω
h_{re}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	-	2.0	-	2.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	40	300	40	300	
h_{oe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	-	300	-	300	μS
$Re(h_{ie})$	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=300\text{MHz}$	-	30	-	30	Ω
t_{on}	$V_{CC}=30\text{V}, I_C=10\text{mA}, I_{B1}=1.0\text{mA}$	-	300	-	300	ns
t_{off}	$V_{CC}=30\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1.0\text{mA}$	-	1.0	-	1.0	ms

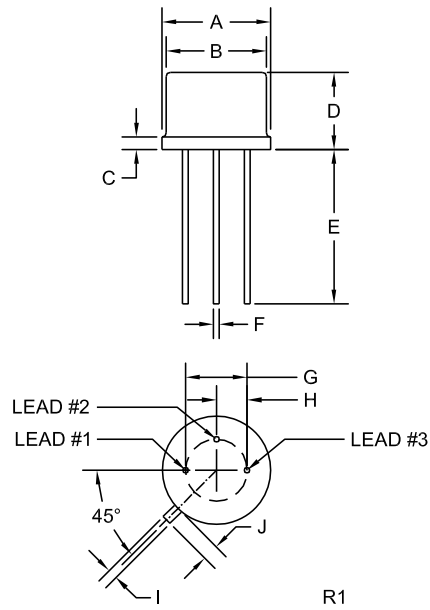
R0 (11-March 2015)

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TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R0 (11-March 2015)